

BSM 50 GD 170 DL

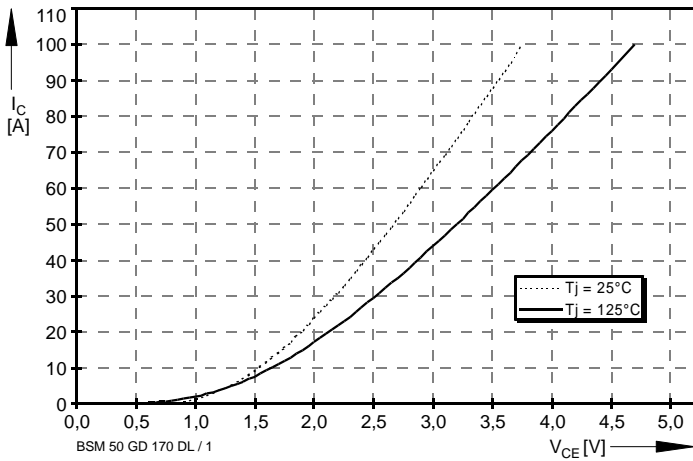


Bild / Fig. 1
Ausgangskennlinie (typisch) /
Output characteristic (typical)
 $I_C = f(V_{CE})$
 $V_{GE} = 15V$

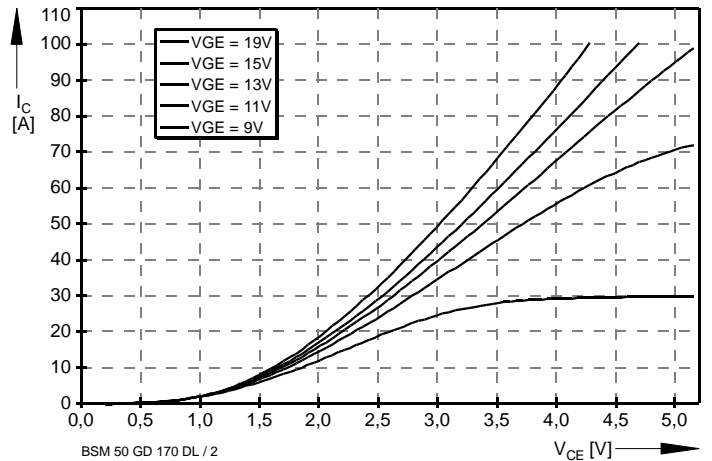


Bild / Fig. 2
Ausgangskennlinienfeld (typisch) /
Output characteristic (typical)
 $I_C = f(V_{CE})$
 $T_{vj} = 125^\circ C$

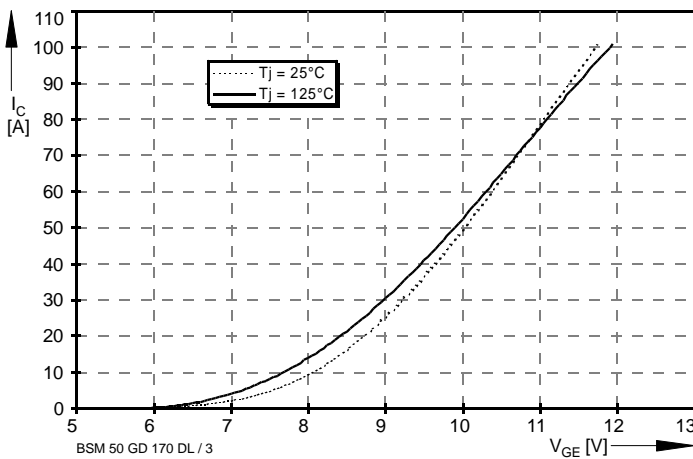


Bild / Fig. 3
Übertragungscharakteristik (typisch) /
Transfer characteristic (typical)
 $I_C = f(V_{GE})$
 $V_{CE} = 20V$

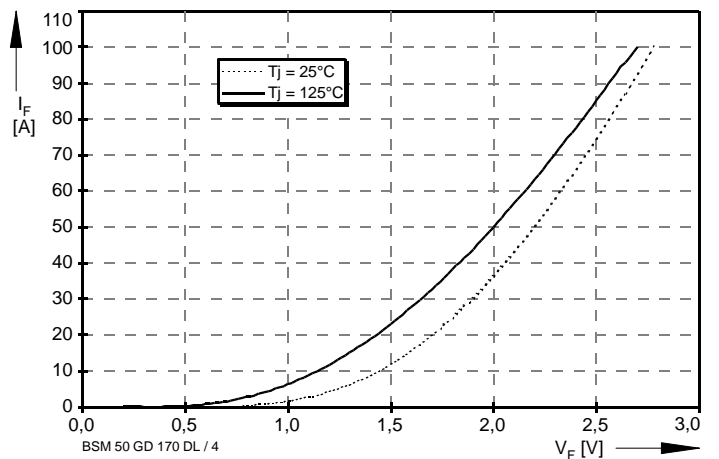


Bild / Fig. 4
Durchlaßkennlinie der Inversdiode (typisch) /
Forward characteristic of inverse diode (typical)
 $I_F = f(V_F)$

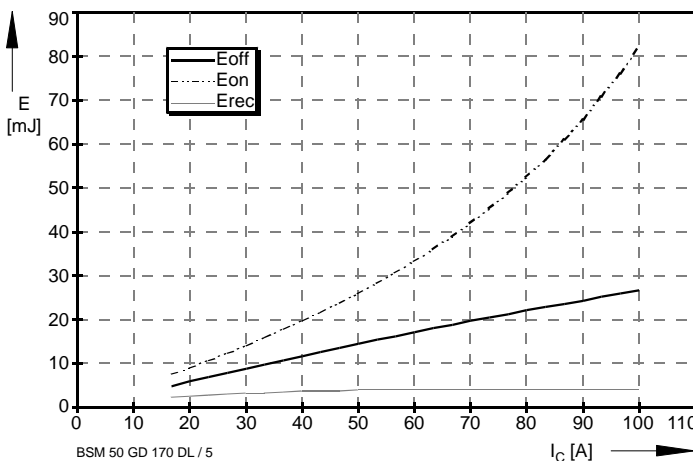


Bild / Fig. 5
Schaltverluste (typisch) /
Switching losses (typical)
 $E_{on} = f(I_C)$, $E_{off} = f(I_C)$, $E_{rec} = f(I_C)$
 $R_{gon} = R_{goff} = 30\Omega$, $V_{CE} = 900V$, $T_j = 125^\circ C$

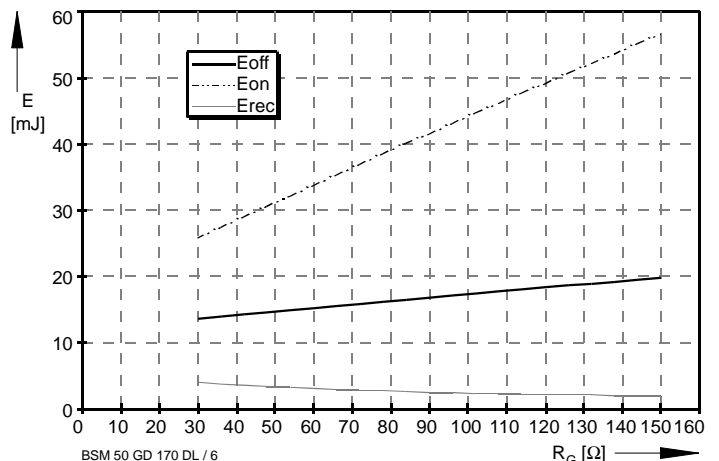


Bild / Fig. 6
Schaltverluste (typisch) /
Switching losses (typical)
 $E_{on} = f(R_G)$, $E_{off} = f(R_G)$, $E_{rec} = f(R_G)$
 $I_C = 50A$, $V_{CE} = 900V$, $T_j = 125^\circ C$

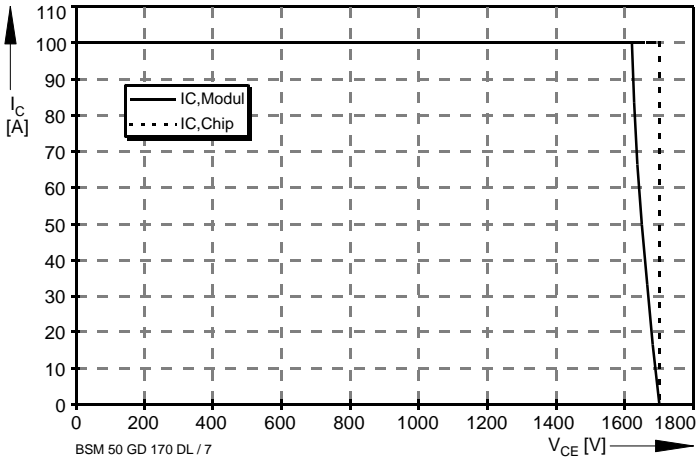


Bild / Fig. 7
Sicherer Arbeitsbereich (RBSOA) /
Reverse bias safe operation area (RBSOA)
 $R_g = 30\Omega$, $T_{vj} = 125^\circ\text{C}$